Title (en)

CONTINUOUSLY PULLED SINGLE CRYSTAL SILICON INGOTS.

Title (de)

KONTINUIERLICH GEZOGENE SILIZIUMEINZELKRISTALLBLÖCKE.

Title (fr)

BARRES DE SILICIUM MONOCRISTALLIN A TIRAGE EN CONTINU.

Publication

EP 0205422 A1 19861230 (EN)

Application

EP 85900367 A 19841204

Priority

US 8401980 W 19841204

Abstract (en)

[origin: WO8603523A1] A method for producing single crystal ingots continuously by forming a molten body of silicon metal of two feedstocks of silicon, one feedstock containing a predetermined level of dopant; continuously drawing a single crystal ingot of doped silicon from said molten body of silicon, said ingot being characterized in that the concentration of dopant is uniform along the length of the ingot, while continuously feeding said feedstocks into said molten body of silicon to thereby maintain the concentration of dopant uniform in said body during the drawing of the single crystal therefrom.

Abstract (fr)

Procédé de production en continu de barres de silicium monocristallin consistant à former un corps en fusion de silicium métal à partir de deux charges de silicium dont l'une contient un degré prédéterminé de dopant, à tirer en continu une barre de silicium dopé monocristallin à partir dudit corps de silicium en fusion, ladite barre étant caractérisée en ce que la concentration de dopant est uniforme sur toute la longueur, tout en introduisant en continu lesdites charges dans ledit corps de silicium en fusion pour ainsi y maintenir uniforme la concentration de dopant durant le tirage du monocristal.

IPC 1-7

C30B 15/04

IPC 8 full level

H01L 21/18 (2006.01); **C30B 15/00** (2006.01); **C30B 15/02** (2006.01); **C30B 15/04** (2006.01); **C30B 29/06** (2006.01)

CPC (source: EP)

C30B 15/002 (2013.01); **C30B 15/02** (2013.01)

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